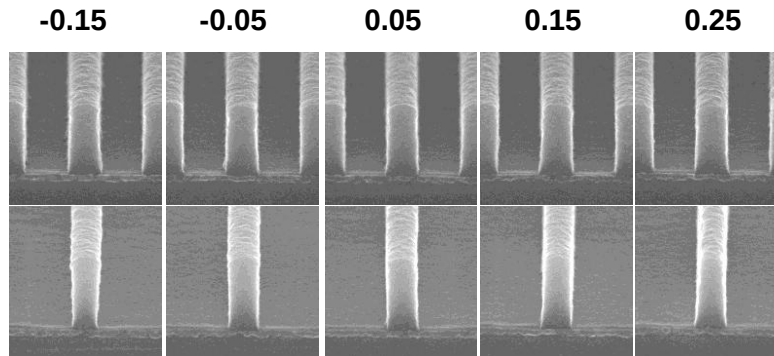
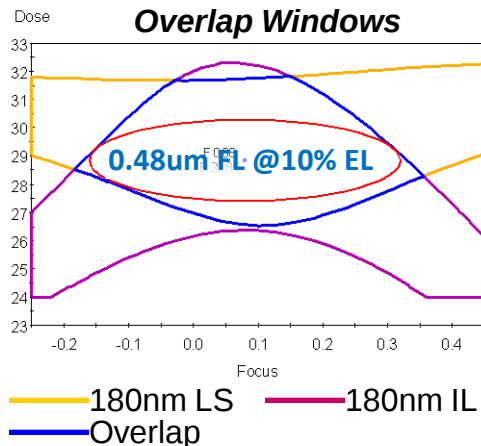


UVTM135G KrF Photoresist

➤ **UV135TM is a high temperature KrF positive photo resist for Consolidation combining Metal, Via and LS application.**

- **Good resolution,**
- **Wide process window margin**
- **Good I/D bias.**
- **Thickness range is 0.35~1.0um thickness.**

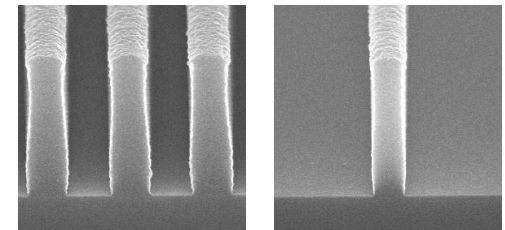
180nm CD @390nm Film Thickness on AR3



Dose : 29.0mJ/cm²

250nm CD @900nm Film Thickness on Bare-Si

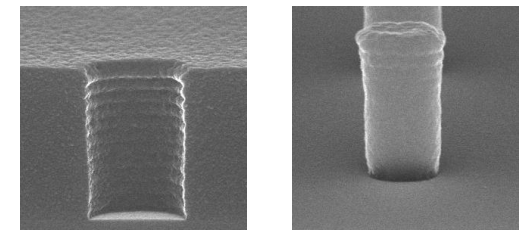
Dense Trench Isolated Line



Dose : 25.0mJ/cm²

500nm CD @825nm Film Thickness on Bare-Si

Iso-CH Iso-DOT



Dose : 22.0mJ/cm²

- Substrate : 150mm Silicon
- Wafer Track : TEL, Mark-8
- Resist Thickness : As indicated
- Soft Bake : 120°C / 60sec
- Exposure : 0.60NA-0.65PC.
- Mask : Binary
- PEB : 130°C / 60sec
- Developer : MF CD-26
- Develop : 23°C / 30sec, SP

- Substrate : 200mm Silicon
- Wafer Track : TEL, ACT-8
- ARC : AR3, T=60nm, 200°C / 60sec
- Resist Thickness : 390nm
- Soft Bake : 120°C / 90sec
- Exposure : ASML, /850, 0.70NA-0.89 PC.
- Mask : Binary
- PEB : 130°C / 90sec
- Developer : MF CD-26
- Develop : 23°C / 60sec, SH Nozzle



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